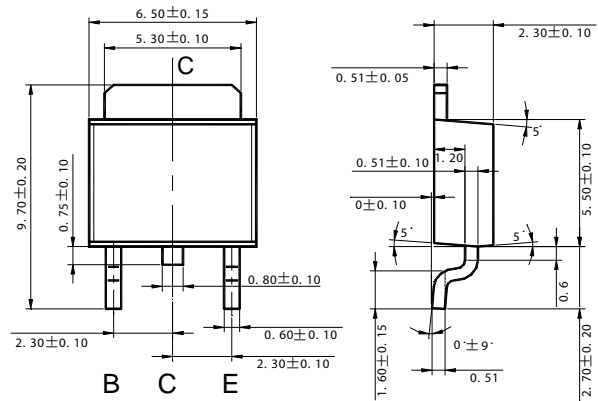


FEATURES

The 2SB1182DX is designed for medium power amplifier application
Low collector saturation voltage: $V_{CE(sat)} = -0.5V$ (Typ.)
RoHS Compliant Product

MARKING : 1182
(With Date Code)

TO-252



MAXIMUM RATINGS* $T_A=25^{\circ}C$ unless otherwise noted

Parameter	Symbol	Value	Units
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-32	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-2	A
Collector Current -Pulse, $P_w=100mS$	I_C	-2	A
Collector Dissipation	P_C	10	W
Junction and Storage Temperature	T_J, T_{stg}	+150, -55~+150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -50\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -50\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20V, I_E = 0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-1	μA
DC current gain	h_{FE}	$V_{CE} = -3V, I_C = -500mA$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -200mA$		-500	-800	V
Transition frequency	f_T	$V_{CE} = -5V, I_C = 500mA, f = 100MHz$		100		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, f = 1MHz$		50		pF

CLASSIFICATION OF h_{FE}

Rank	P	Q	R
Range	82 - 180	120 - 270	180 - 390

Electrical characteristic curves

